

Hengze Qu

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/5411481/publications.pdf>

Version: 2024-02-01

15
papers

316
citations

933447

10
h-index

996975

15
g-index

15
all docs

15
docs citations

15
times ranked

253
citing authors

#	ARTICLE	IF	CITATIONS
1	Extending Channel Scaling Limit of p-MOSFETs Through Antimonene With Heavy Effective Mass and High Density of State. IEEE Transactions on Electron Devices, 2022, 69, 857-862.	3.0	17
2	Enhanced interband tunneling in two-dimensional tunneling transistors through anisotropic energy dispersion. Physical Review B, 2022, 105, .	3.2	16
3	A Machine Learning Approach for Optimization of Channel Geometry and Source/Drain Doping Profile of Stacked Nanosheet Transistors. IEEE Transactions on Electron Devices, 2022, 69, 3568-3574.	3.0	10
4	High-Performance and Low-Power Transistors Based on Anisotropic Monolayer Te_2O . Physical Review Applied, 2022, 17, .	3.8	15
5	Uncovering the Anisotropic Electronic Structure of 2D Group VA-VA Monolayers for Quantum Transport. IEEE Electron Device Letters, 2021, 42, 66-69.	3.9	31
6	Quantum Transport in Monolayer InAs Field-Effect Transistors. Advanced Electronic Materials, 2021, 7, 2001169.	5.1	6
7	First-principle study of puckered arsenene MOSFET. Journal of Semiconductors, 2020, 41, 082006.	3.7	4
8	Ultrascaled Double-Gate Monolayer SnS_2 MOSFETs for High-Performance and Low-Power Applications. Physical Review Applied, 2020, 14, .	3.8	21
9	Ballistic Transport in High-Performance and Low-Power Sub-5 nm Two-Dimensional ZrNBr MOSFETs. IEEE Electron Device Letters, 2020, 41, 1029-1032.	3.9	14
10	Anisotropic InP Plane Ballistic Transport in Monolayer Black Arsenic-Phosphorus FETs. Advanced Electronic Materials, 2020, 6, 1901281.	5.1	59
11	Designing sub-10-nm Metal-Oxide-Semiconductor Field-Effect Transistors via Ballistic Transport and Disparate Effective Mass: The Case of Two-Dimensional Bi_2N . Physical Review Applied, 2020, 13, .	3.8	69
12	DFT coupled with NEGF study of the electronic properties and ballistic transport performances of 2D Sb_3Te_3 . Nanoscale, 2020, 12, 9958-9963.	5.6	11
13	Ballistic Quantum Transport of Sub-10 nm 2D $\text{Sb}_2\text{Te}_2\text{Se}$ Transistors. Advanced Electronic Materials, 2019, 5, 1900813.	5.1	14
14	Unusual Electronic Transitions in Two-dimensional Layered SnSb_2 Driven by Electronic State Rehybridization. Physical Review Applied, 2019, 11, .	3.8	21
15	Electronic structure and transport properties of 2D RhTeCl : a NEGF-DFT study. Nanoscale, 2019, 11, 20461-20466.	5.6	8